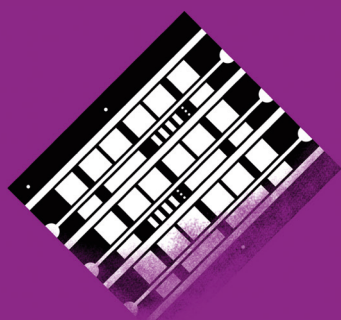
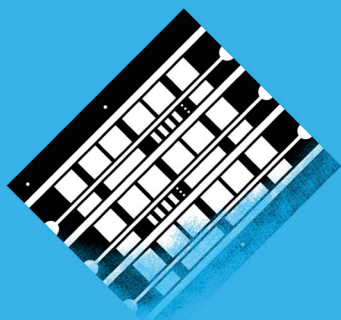


# Relation between growth rate, material quality, and device grade condition for intrinsic microcrystalline silicon:

From layer investigation to the application to thin-film tandem solar cells

Stephan Yann Michard



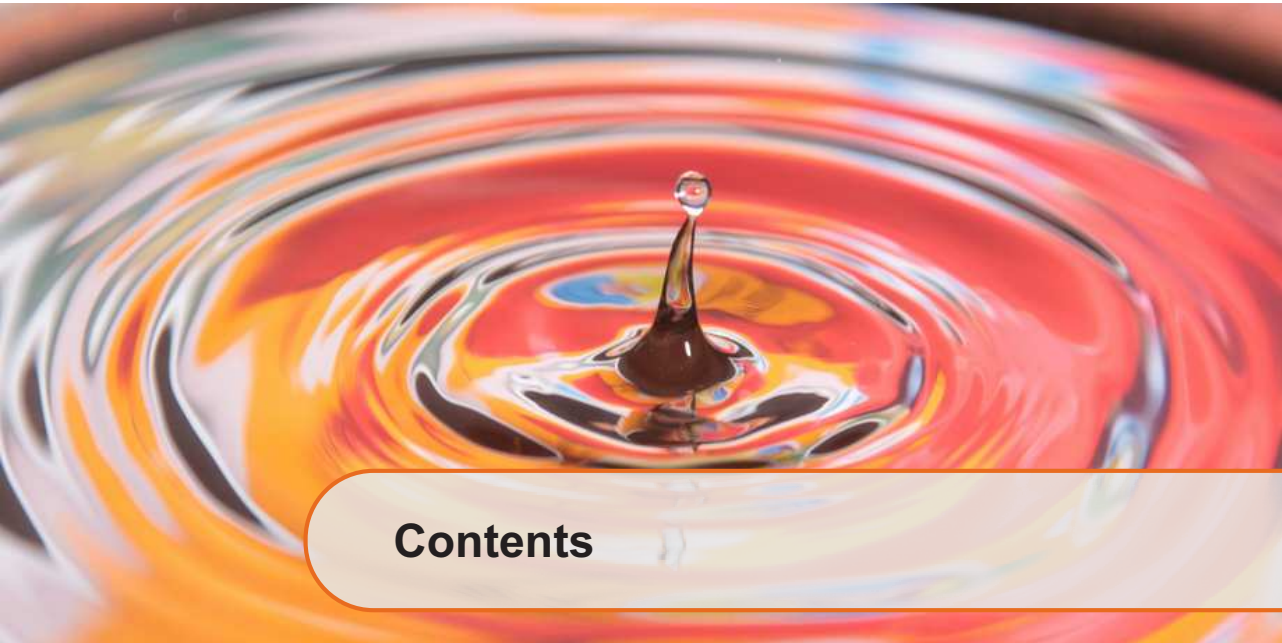
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A high-speed photograph of a water droplet hitting a surface, creating a series of concentric ripples. The water is a vibrant red color. A white, rounded rectangular label with the word 'Contents' in black text is positioned in the lower right corner of the image.

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